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SPECIFICATION

TITLE

"DEVICE TRANSFER METHOD AND PANEL"

BACKGROUND OF THE INVENTION

The present invention relates to a device transfer method of transferring light emitting devices such as light emitting diodes, which have been formed on a substrate, for example, a sapphire substrate, to a device transfer body such as a display panel, and to a panel on which the transferred devices are arrayed.

A known method of producing an LED (Light Emitting Diode) display using LEDs includes the steps of cutting an LED wafer, which is obtained by stacking semiconductor layers on a device formation substrate, into chips by a diamond blade or the like, and transferring the LED chips to a display panel or the like with a pitch larger than an array pitch of the LED chips on the device formation substrate.

The above-described cutting method, however, has problems. For example, blue light emitting diodes are produced by stacking gallium nitride based semiconductor layers on a sapphire substrate as a device formation substrate. In this case, sapphire used as the material of the substrate is as very hard, about 9 in Mohs' hardness. As a result, if the sapphire substrate is full cut into chips by a dicer such as a diamond blade, problems such as cracking and/or chipping tend to occur in the cut planes of the sapphire substrate which prevent the sapphire substrate from being smoothly cut into chips of desired shapes and sizes, the dicer itself may also be broken, and that since sapphire has no cleavage characteristic, it is difficult to cut the sapphire substrate into chips by forming scribing lines on the sapphire substrate and forcibly cutting the sapphire substrate along the scribing lines by an external force.

To solve the above problems, a method of cutting a sapphire substrate has been disclosed, for example, in Japanese Patent Laid-open No. Hei 5-315646. According to this method, as shown in FIG. 12, a gallium nitride semiconductor layer 61 formed on a sapphire substrate 60 is cut by a dicer to form grooves 62 deeper than a thickness of the gallium nitride semiconductor layer 61. The sapphire substrate 60 is thinned by polishing a back surface of the sapphire substrate 60. Scribing lines 63 are formed on the sapphire substrate 60 via the grooves 62 by a scriber. The sapphire

substrate 60 is then forcibly cut into chips by an external force. This document describes how the sapphire substrate can be smoothly cut into chips without occurrence of cracking and/or chipping in the cut planes of the sapphire substrate 50. However, such a cutting method, requires several steps including the labor intensive step of polishing the sapphire substrate 60. In other words, the above method of cutting a sapphire substrate 60 is expensive and time consuming.

If a larger number of LED devices are obtained from one device formation substrate, the cost of one LED device can be reduced and the cost of a display unit using such LED devices can be also reduced. In the method disclosed in the above document, Japanese Patent Laid-open No. Hei 5-315646, LED devices each having a size of 350 μ m per side are obtained from the sapphire substrate having a diameter of two inches. If LED devices each having a size of several tens μ m per side are obtained from the sapphire substrate having a diameter of two inches and a display unit is produced by transferring the LED devices on a display panel, it is possible to reduce the cost of a display unit.

However, if the size of each LED device becomes as small as several tens of μ m per side, it becomes difficult to handle the LED device in the transfer step. Further, since an electrode of each device to be connected to a wiring layer of a base body of a display panel becomes small, the connection work becomes difficult and also a connection failure may often occur.

SUMMARY OF THE INVENTION

An object of the present invention is to provide a device transfer method capable of easily, smoothly separating devices from each other, and facilitating handling of devices in a transfer step and ensuring good electrical connection between the devices and external wiring, although the devices are fine devices, and to provide a panel on which the transferred devices are arrayed.

To achieve the above object, according to a first aspect of the present invention, a device transfer method is provided, the method includes covering a plurality of devices, formed on a substrate, with a layer of resin; the resin layer is then cut, to obtain resin buried devices each of which contains at least one of the devices. The resin buried devices are then peeled from the substrate and transferred to a device transfer body.

* The following are the names of the persons who have been elected to the office of Justice of the Peace for the year ending March 31, 1908.

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resin layer to obtain resin buried devices each containing at least one of the devices. The resin buried devices are peeled from the second supporting board, and transferred to a device transfer body.

With this configuration, the resin buried device being handled has a size larger than that of the device itself. The larger size of the resin buried device facilitates the handling of the devices in the transfer step. Since the electrode is formed in the first and second resin layers in such a manner as to be connected to the device, it is possible to easily form the electrode and to prevent occurrence of connection failures between the electrode and an external electrode by increasing the area of the electrode. Since respective resin buried devices are obtained by cutting only the first and second resin layers without the need of cutting the substrate, it is possible to easily obtain the resin buried devices because the first and second resin layers can be easily, smoothly cut. Further, the substrate, which is not cut, can be reused.

According to a fourth aspect of the present invention, a panel including an array of resin buried devices is provided. Resin buried device contains at least one device. A plurality of the devices are formed on a substrate and are covered with a resin layer. The resin layer is cut to obtain the resin buried devices each containing at least one of the devices. Furthermore, the resin buried devices are peeled from the substrate and are transferred to the panel.

With this configuration, it is possible to provide an inexpensive panel.

In the above device transfer method, preferably, connection holes are formed in the resin layer in a manner such as to reach the devices by laser beams, and the electrodes are connected to the devices via the connection holes. With this configuration it is possible to prevent the resin layer covering the device from being thinned and hence to improve the strength of the resin buried device.

In the device transfer method, preferably, the electrodes are each formed with their planar dimension substantially corresponding to a planar dimension of each of the resin buried devices, and the resin layer is cut by laser beams with the electrodes taken as a mask, to obtain the resin buried devices. With this configuration, it is possible to eliminate the need of use of a laser system having a high accurate positioning function and hence to reduce the production cost of the devices.

$$x_1 = \begin{bmatrix} 1 \\ 0 \\ 0 \\ 0 \end{bmatrix}, x_2 = \begin{bmatrix} 0 \\ 1 \\ 0 \\ 0 \end{bmatrix}, x_3 = \begin{bmatrix} 0 \\ 0 \\ 1 \\ 0 \end{bmatrix}, x_4 = \begin{bmatrix} 0 \\ 0 \\ 0 \\ 1 \end{bmatrix}, x_5 = \begin{bmatrix} 1 \\ 1 \\ 1 \\ 1 \end{bmatrix}, x_6 = \begin{bmatrix} 1 \\ 1 \\ 1 \\ 0 \end{bmatrix}, x_7 = \begin{bmatrix} 1 \\ 1 \\ 0 \\ 1 \end{bmatrix}, x_8 = \begin{bmatrix} 1 \\ 1 \\ 0 \\ 0 \end{bmatrix}, x_9 = \begin{bmatrix} 1 \\ 0 \\ 1 \\ 1 \end{bmatrix}, x_{10} = \begin{bmatrix} 1 \\ 0 \\ 1 \\ 0 \end{bmatrix}, x_{11} = \begin{bmatrix} 1 \\ 0 \\ 0 \\ 1 \end{bmatrix}, x_{12} = \begin{bmatrix} 1 \\ 0 \\ 0 \\ 0 \end{bmatrix}, x_{13} = \begin{bmatrix} 0 \\ 1 \\ 1 \\ 1 \end{bmatrix}, x_{14} = \begin{bmatrix} 0 \\ 1 \\ 1 \\ 0 \end{bmatrix}, x_{15} = \begin{bmatrix} 0 \\ 1 \\ 0 \\ 1 \end{bmatrix}, x_{16} = \begin{bmatrix} 0 \\ 1 \\ 0 \\ 0 \end{bmatrix}, x_{17} = \begin{bmatrix} 0 \\ 0 \\ 1 \\ 1 \end{bmatrix}, x_{18} = \begin{bmatrix} 0 \\ 0 \\ 1 \\ 0 \end{bmatrix}, x_{19} = \begin{bmatrix} 0 \\ 0 \\ 0 \\ 1 \end{bmatrix}, x_{20} = \begin{bmatrix} 0 \\ 0 \\ 0 \\ 0 \end{bmatrix}$$

100-24179-40 100-24179-41 100-24179-42 100-24179-43 100-24179-44 100-24179-45 100-24179-46 100-24179-47 100-24179-48 100-24179-49 100-24179-50 100-24179-51 100-24179-52 100-24179-53 100-24179-54 100-24179-55 100-24179-56 100-24179-57 100-24179-58 100-24179-59 100-24179-60 100-24179-61 100-24179-62 100-24179-63 100-24179-64 100-24179-65 100-24179-66 100-24179-67 100-24179-68 100-24179-69 100-24179-70 100-24179-71 100-24179-72 100-24179-73 100-24179-74 100-24179-75 100-24179-76 100-24179-77 100-24179-78 100-24179-79 100-24179-80 100-24179-81 100-24179-82 100-24179-83 100-24179-84 100-24179-85 100-24179-86 100-24179-87 100-24179-88 100-24179-89 100-24179-90 100-24179-91 100-24179-92 100-24179-93 100-24179-94 100-24179-95 100-24179-96 100-24179-97 100-24179-98 100-24179-99 100-24179-100

FIGS. 6A to 6C are sectional views showing steps continued from FIG. 5C, wherein FIG. 6A shows a state in which an electrode connected to each device is

formed, FIG. 6B shows a state in which the resin layers are cut by laser beams, and FIG. 6C shows a state in which resin buried devices are peeled from the third supporting board;

FIGS. 7A and 7B are sectional views showing steps continued from FIG. 6C, wherein FIG. 7A shows a state in which each resin buried body is bonded to a device transfer body, and FIG. 7B shows a state in which a resin buried device of another kind is bonded to the same device transfer body;

FIGS. 8A and 8B are sectional views showing steps continued from FIG. 7B, wherein FIG. 8A shows a state in which an interlayer insulating film is formed, and FIG. 8B shows a state in which wiring is formed;

FIGS. 9A to 9D are sectional views showing steps continued from the step shown in FIG. 3C, according to a second embodiment of the present invention, wherein a connection hole is formed in the resin layers by laser beams;

FIGS. 10A and 10B are sectional views showing steps continued from the step shown in FIG. 5C, according to a third embodiment, wherein the resin layers are cut by laser means with the electrode taken as a mask;

FIGS. 11A and 11B are views showing a light emitting device used in the embodiments of the present invention, wherein FIG. 11A is a sectional view and FIG. 11B is a plan view; and

FIG. 12 is a sectional view showing a related art method of cutting a gallium nitride based semiconductor wafer.

DETAILED DESCRIPTION OF THE INVENTION

Hereinafter, embodiments of the present invention will be described in detail with reference to the accompanying drawings.

First, there will be described devices used for carrying out the present invention with reference to FIGS. 11A and 11B, which devices are exemplified by light emitting diodes representative of light emitting devices in the following embodiments. FIG. 11A is a sectional view of such a light emitting diode and FIG. 11B is a plan view of the light emitting diode. As shown in these figures, a light emitting diode 2 is made from a gallium nitride (GaN) based semiconductor and is formed by crystal growth on a device formation substrate, for example, a sapphire substrate 1.

An under growth layer 51 made from a GaN based semiconductor is formed on the sapphire substrate 1, and a hexagonal pyramid shaped GaN layer 52 doped with silicon is formed on the under growth layer 51 as follows: namely, an insulating film 53 is formed on the under growth layer 51, and a GaN layer 52 for one device is selectively grown, by an MOCVD (Metal-organic Chemical Vapor Deposition) process, from one of openings formed in the insulating film 53 in such a manner as to be separated from a GaN layer 52 for another device. In the case of taking a C-plane of sapphire as a principal plane of the sapphire substrate 1, the GaN layer 52 becomes a hexagonal pyramid shaped growth layer surrounded by an S-plane, that is, a (1-101) plane 52a.

A portion of the inclined S-plane 52a of the GaN layer 52 functions as a cladding of a double-hetero structure. An InGaN layer 54 is formed as an active layer on the GaN layer 52 in such a manner as to cover the S-plane 52a. A GaN layer 55 doped with magnesium is formed on the InGaN layer 54. The GaN layer 55 functions as a cladding.

A metal material such as Ni, Pt, Au, or Pb is vapor-deposited on the GaN layer 55, to form a p-electrode 56. An n-electrode will be formed on a back surface side of the under growth layer 51 during a transfer step to be described later.

The above described light emitting diode 2 is configured, for example, as a light emitting diode of blue (B). The structure of the light emitting diode 2 is not limited to that described above but may be a structure in which an active layer is formed into a flat plate or band shape, or be a pyramid structure with a C-plane formed on its upper end portion. The material of the light emitting diode 2 is not limited to a GaN based material, either, but may be any other nitride based material or any other compound semiconductor.

A device transfer method according to a first embodiment of the present invention will be described below with reference to FIGS. 1 to 8. The light emitting diodes 2 shown in FIGS. 11A and 11B are used as devices to be transferred by the device transfer method according to the first embodiment.

Referring to FIG. 1A, a plurality of light emitting diodes 2, each having the same structure as that shown in FIGS. 11A and 11B, are densely formed on a principal plane of a sapphire substrate 1 having a diameter of, for example, two inches in such a manner as to be arrayed in rows and columns, that is, into a matrix. Each light

emitting diode 2 has a size about 20 μ m square. The light emitting diodes 2 are in a state being separable from each other by device separation grooves 4 formed by reactive ion etching or the like.

The sapphire substrate 1 is coated with an ultraviolet curing type resin 3, and a polyimide layer 6 formed on a surface of a quartz glass board 5 as a first supporting board is brought into press-contact with the ultraviolet curing type resin 3.

Referring to FIG. 1B, the ultraviolet curing type resin 3 is irradiated with ultraviolet rays having come from a back surface side of the quartz glass board 5 side, to be hardened, whereby a first resin layer 3' is formed. The light emitting diodes 2 are thus collectively covered with the first resin layer 3'.

Referring to FIG. 1C, interfaces between the GaN based under growth layers 51 of the light emitting diodes 2 and the sapphire substrate 1 are irradiated with laser beams having come from a back surface side of the sapphire substrate 1. At this time, GaN at each interface is decomposed into nitrogen and gallium and the gaseous nitrogen is released therefrom, so that the bond of each light emitting diode 2 to the sapphire substrate 1 is released. Consequently, as shown in FIG. 2A, the light emitting diodes 2 are collectively peeled from the sapphire substrate 1. With respect to the first resin layer 3' covering the light emitting diodes 2, bonds of molecules constituting the resin layer 3' are cut at the interfaces by the same laser abrasion effect. As a result, the resin layer 3' is peeled, together with the light emitting diodes 2, from the sapphire substrate 1.

As shown in FIG. 2A, only gallium (Ga) 7 remains on the peeling surface on the light emitting diode 2 side, which gallium is then removed by wet etching or the like as shown in FIG. 2B.

Referring to FIG. 2C, device separation grooves 8, each extending from the device separation groove 4 to the quartz glass board 5, are formed by etching the first resin layer 3' by using oxygen plasma. The formation of the device separation grooves 8 makes the light emitting diodes 2 separable from each other. In this plasma etching, since an erosion effect of oxygen plasma to the under growth layer 51 is significantly smaller than that to the first resin layer 3', the device separation grooves 8 are formed with the under growth layer 51 taken as a mask.

Referring to FIG. 3A, the light emitting diodes 2 covered with the first resin layer 3' are coated with an ultraviolet curing type resin 9, and a polyimide layer 11

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As shown in FIG. 4B, the second resin layer 12, the polyimide layer 6, and the first resin layer 3' are etched back by using oxygen plasma, to expose the p-electrode 56 of the light emitting diode 2, and then the surfaces of the p-electrode 56 and the first and second resin layers 3' and 12, on which an extraction electrode to be described later is to be formed, are cleaned.

Referring to FIG. 4C, an extraction electrode 13 is formed on the first and second resin layers 3' and 12 in such a manner as to be connected to the p-electrode 56 of the light emitting diode 2. The extraction electrode 13 is formed by depositing a transparent material made from a metal or ITO (Indium Tin Oxide) by vapor-deposition or sputtering and patterning the deposited material into a specific planar shape having a specific size by photolithography and wet etching.

Referring to FIG. 5A, a quartz glass board 14 as a third supporting board is fixed to a surface side, on which the extraction electrode 13 has been formed, of the second resin layer 12 via a polyimide layer 15 formed on a surface of the quartz glass board 14. An interface between the polyimide layer 11 and the quartz glass board 10 is irradiated with laser beams having come from a back surface side of the quartz glass board 10, so that the polyimide layer 11 is peeled from the quartz glass board 10 or internally peeled by the laser abrasion effect (see FIG. 5B). In this way, the light emitting diodes 2 on the quartz glass board 10 as the second supporting board are collectively transferred, together with the resin layers 3' and 12 covering the light emitting diodes 2, to the quartz glass board 14 as the third supporting board. As will be described below, this transfer step is carried out for forming an extraction electrode on the n-electrode side opposite to the extraction electrode 13 on the p-electrode side.

Referring to FIG. 5C, the polyimide layer 11 and the second resin layer 12 are etched back by oxygen plasma, to expose the under growth layer 51 of the light emitting diode 2, and then surfaces of the under growth layer 51 and the second resin layer 12, on which an extraction electrode on the n-electrode side is to be formed as described below, are cleaned.

Referring to FIG. 6A, an extraction electrode 16 is formed on the second resin layer 12 in such a manner as to be connected to the under growth layer 51 of the light emitting diode 2. The extraction electrode 16 is formed by depositing a transparent material such a metal or ITO by vapor-deposition or sputtering and patterning the

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$$= \frac{1}{n} \sum_{j=1}^n \left(\frac{\partial}{\partial \theta} \log f_j(\theta) \right)^T \frac{\partial}{\partial \theta} \log f_j(\theta) = \frac{1}{n} \sum_{j=1}^n \left(\frac{\partial}{\partial \theta} \log f_j(\theta) \right)^T \frac{\partial}{\partial \theta} \log f_j(\theta)$$

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reduce the product cost of one light emitting diode and hence to reduce the cost of a display unit using the light emitting diodes. Since the light emitting diode is transferred to the device transfer body 50 in the form of the resin buried device having the size about 160 μ m square, it is possible to easily handle the light emitting diodes in the transfer step. The resin layer covering the light emitting diode 2 serves to protect the light emitting diode. The enlargement of the size of the light emitting diode 2 by covering the diode 2 with the resin layer is advantageous in that the extraction electrodes 13 and 16 can be easily formed, and that the planar sizes of the extraction electrodes 13 and 16 can be enlarged enough to prevent occurrence of any wiring failure at the time of wiring the extraction electrodes 13 and 16 to the device transfer body 50 side, to improve the reliability of wiring thereof to the device transfer body 50 side.

In the above embodiment, in place of cutting the hard sapphire substrate 1, the first and second resin layers 3 and 12 are cut by laser beams, to separate an array of the light emitting diodes 2 into individual devices to be transferred (resin buried devices). With this configuration, since the resin layer can be easily and accurately cut by the laser abrasion effect, it is possible to separate an array of the light emitting diodes 2 into individual devices having accurate shapes and sizes without a lot of labor and time paid for cutting.

A second embodiment of the present invention will be described with reference to FIGS. 9A to 9D. It is to be noted that parts corresponding to those described in the first embodiment are designated by the same reference numerals and the overlapped description thereof is omitted.

FIG. 9A shows a step equivalent to the step shown in FIG. 4A according to the first embodiment. According to this embodiment, however, the process goes on from the step shown in FIG. 9A to a step shown in FIG. 9B, in which the second resin layer 12, the polyimide layer 6 and the first resin layer 3' are etched back by oxygen plasma to an extent that the p-electrode 56 of the light emitting diode 2 is not exposed, and then the surfaces of the first and second resin layers 3' and 12, on which an extraction electrode to be described later is to be formed, are cleaned.

Referring to FIG. 9C, a connection hole 23 is formed in the first resin layer 3' by laser beams emitted by an excimer laser system or a third harmonic YAG laser system, to expose the p-electrode 56 of the light emitting diode 2. Referring to FIG.

9D, an extraction electrode 13' is formed on the first and second resin layers 3' and 12 in such a manner as to be connected to the p-electrode 56 via the connection hole 23. The material of the extraction electrode 13' and the formation method thereof are the same as those described in the first embodiment. Subsequent steps are also the same as those described in the first embodiment.

According to the first embodiment, as shown in FIG. 4B, the first and second resin layers 3' and 12 are etched back until the p-electrode 56 is exposed, and correspondingly, the thicknesses of the first and second resin layers 3' and 12 for covering and protecting the light emitting diode 2 become thin, so that the rigidity of the resin buried device 20 obtained in the subsequent step becomes weak. This may often cause a difficulty in handling the resin buried device 20 at the time of picking up the resin buried device 20 by the vacuum chuck 21 for transferring it to the device transfer body 50.

To cope with such an inconvenience, according to the second embodiment, as described above, the connection hole 23 for exposing the p-electrode 56 therethrough is locally formed in the first and second resin layers 3' and 12, with a result that as compared with the first embodiment, the thickness of the first and second resin layers 3' and 12 become thicker and thereby the strengths thereof become larger. Another advantage of formation of the connection hole 23 is as follows. Since an etching rate of the ultraviolet curing resin forming each of the first and second resin layers 3' and 12 by oxygen plasma is small, it takes a lot of time to etch back the first and second resin layers 3' and 12. Meanwhile, the use of laser beams can form the connection hole in a resin layer for a short time irrespective of a material forming the resin layer. Accordingly, as compared with the manner in the first embodiment that the first and second resin layers 3' and 12 are etched back by oxygen plasma until the p-electrode 56 is exposed, the manner in the second embodiment that the first and second resin layers 3' and 12 are etched back by oxygen plasma to an extent that the p-electrode 56 is not exposed and then the connection hole 23 is formed in the first and second resin layers 3' and 12 by laser beams so as to expose the p-electrode 56 therethrough is advantageous in that the time required to expose the p-electrode 56 can be shortened, and that the degree of freedom in selection of materials for forming the first and second resin layers 3' and 12 can be increased, leading to the reduced material cost.

It to be noted that the step shown in FIG. 9B may be replaced with a step in which the connection hole 23 is directly formed in the second resin layer 12, the polyimide layer 6, and the first resin layer 3' in the state shown in FIG. 9A. However, the cleaning of the surfaces, on which the extraction electrode 13' is to be formed, by oxygen plasma as in the step shown in FIG. 9B is advantageous in increasing the adhesive strength of the extraction electrode 13' to the resin layers.

A third embodiment of the present invention will be described below with reference to FIGS. 10A and 10B. It is to be noted that parts corresponding to those described in the first embodiment are designated by the same reference numerals and the overlapped description thereof is omitted.

According to the third embodiment, the process goes on from the step shown in FIG. 5C in the first embodiment to a step shown in FIG. 10A, in which an extraction electrode 16' to be connected to the under growth layer 51 of the light emitting diode 2 is formed on the second resin layer 12, wherein a planar size of the extraction electrode 16' is set to be equal to that of a resin buried device 20' obtained in the next step, that is, set to a square shape having a size 160 μ m square. Like the first embodiment, the extraction electrode 16' is formed by depositing a transparent material such as a metal or ITO by sputtering and patterning the deposited material into a planar shape having the above-described specific size by photolithography and wet etching.

In the next step shown in FIG. 10B, device separation grooves 17 are formed by cutting the second resin layer 12 and the polyimide layer 15 by laser beams L emitted from an excimer laser system or a third harmonic YAG laser system with the extraction electrode 16' taken as a mask, to obtain each resin buried device 20' in which the light emitting diode 2 is covered with the resin layer. Subsequent steps are the same as those described in the first embodiment.

In the step shown in FIG. 6B according to the first embodiment, the device separation grooves 17 are formed by identifying alignment marks formed, for example, at diagonal positions on the laser system side and performing accurate NC control of the laser system on the basis of the identified alignment marks. In this case, the laser system side must be operated at a high positioning accuracy in the order of 1 μ m. On the contrary, according to the third embodiment, since the extraction electrode 16' is formed so as to have the same planar shape and planar size as those of the resin buried

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growth layer may be a material layer containing a light emission region composed of a first conductive layer, an active layer, and a second conductive layer. In particular, the crystal growth layer, preferably and thereby not limited thereto, has a wurtzite crystal structure. Such a crystal layer can be made from, for example, a group III based compound semiconductor, a BeMgZnCdS based compound semiconductor, a BeMgZnCdO based compound semiconductor, a gallium nitride based compound semiconductor, an aluminum nitride (AlN) based compound semiconductor, indium nitride (InN) based compound semiconductor, an indium gallium nitride (InGaN) based compound semiconductor, or aluminum gallium nitride (AlGaN) based compound semiconductor. In particular, a nitride based semiconductor such as a gallium nitride based compound semiconductor is preferably used as the material for forming the above crystal layer. It is to be noted that InGaN or AlGaN, or GaN does not necessarily mean only a nitride based semiconductor of ternary mixed crystal or binary mixed, but may be a nitride based semiconductor containing other impurities in amounts not to affect the nitride based semiconductor. For example, InGaN may contain Al and another impurity in slight amounts not to affect InGaN.

In the light emitting diode described in the embodiments, the peeling layer to be interposed between the substrate and the device is made from polyimide; however, it may be made from another resin, particularly, a high molecular resin. Examples of the high molecular resins may include polyacetylene, polyamide, polyether sulphone, polycarbonate, polyethylene, polyethyleneterephthalate, polymethyl methacrylate, polystyrene, polyvinyl chloride, polyester, polyether, epoxy resin, polyolefin, and polyacrylate. These materials may be used singly or in combination of two or more kinds.

Although each of the first and second resin layers 3' and 12 is made from an ultraviolet curing type resin in the embodiments, it may be made from a thermoplastic resin or a thermosetting resin. The use of an ultraviolet curing type resin, however, is advantageous in that since an ultraviolet curing type resin does not require any heat at the hardening stage, it is not thermally contracted or expanded. As a result, the device is not affected by a stress caused by hardening the resins forming the first and second resin layers 3' and 12, and can be produced at a high dimensional accuracy.

Each of the first, second, and third supporting boards 5, 10 and 14 is not limited to the quartz glass board described in the embodiments, but may be a board of another type, for example, a plastic board.

The transfer of the resin buried devices 20 to the device transfer body 50 may be performed in accordance with a manner different from that described in the embodiment. Specifically, the resin buried devices 20 may be individually peeled from the third supporting board 14 once, and then transferred to the device transfer body 50 one by one.

It is to be noted that the third embodiment may be combined with the second embodiment.

While a preferred embodiment of the present invention has been described using specific terms, such description is for illustrative purposes only, and it is to be understood that changes and variations may be made without departing from the spirit or scope of the following claims.

It should be understood that various changes and modifications to the presently preferred embodiments described herein will be apparent to those skilled in the art. Such changes and modifications can be made without departing from the spirit and scope of the present invention and without diminishing its intended advantages. It is therefore intended that such changes and modifications be covered by the appended claims.